

CE mark opens door to Europe for Aeronex

Aeronex has completed the conformity assessments and compliance testing to meet the EU pressure equipment directive for its standard gas purifiers and class 4 vessels used for bulk purification. In addition, the company's Infinity gas purification system has been certified as complying with the EU electromagnetic compliance and low voltage directives. The company's products can now be labeled with the CE mark, a requirement for sales in the European Union.

Epichem rebrands

Epichem has rebranded its four main product lines to acknowledge the common ownership of the product lines. The group's products will now be listed as Epichem Gases, Epichem Metalorganics, Epichem Oxides & Nitrides, and Epichem Surface Coatings.

The oxides and nitrides product group includes Inorgtech, which was acquired by Epichem in February, 2000, and manufactures precursors for barrier layers, high k dielectrics and ferroelectric thin films.

Plasma etch for biochips

Tegal Corp. has announced the sale of a 903e plasma etch system to Zyomyx, Inc., for making biochip components used in high-throughput, massively parallel protein analysis systems. It was selected by Zyomyx based on superior process results, versatile process flexibility, and on Tegal's reputation for customer support. Tegal expects to install the etch system in early January 2003.

Specialist electronics website from Air Products

The Electronics Division of Air Products has launched a comprehensive website for its customers around the world. Visitors can find information about the entire product and services portfolio which encompasses all the consumable products that surround the

process tool in semiconductor manufacturing.

The company's global reach is now based on eight major offerings: MEGASYS® total gas and chemical management, electronic specialty gases, bulk gases, electronic chemicals, UHP equipment, TRIMEGA,

analytical services, and micro-electronics applications.

Information can be retrieved by product or application. In addition PDF product and material safety data sheets can be downloaded.

The site is found at www.air-products.com/electronics



ICSI3, Third International Conference on SiGe(C) Epitaxy and Heterostructures

www.icsi3.org

Santa Fe New Mexico, March 9 –12th, 2003

Invited Speakers

Topics

Conference chair

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Late News papers

Deadline Feb 16th, 2003

Early Registration

(save ~\$50) deadline
February 9th, 2003

Hotel reservation

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Paul Kempf
Holger Juergensen
Gene Fitzgerald
Nelson Rowell
Klara Lyutovich
Naoharu Sugiyama
Doug Paul
Wei Xin Ni
Didier Dutartre
Larry Larson
Ken Rim
Tony Peaker
Doug Meyer

IBM
Intel
Jazz Semi
AIXTRON
AmberwaveSystems
NRC Canada
U of Stuttgart
Toshiba & MIRAI
Cambridge University
University of Linköping
ST Microelectronics
UC San Diego
IBM
UMIST
ATMI

350GHz SiGe BiCMOS Technology
SiGe technology for 90nm Strained CMOS
Manufacturable 200GHz SiGe BiCMOS
Si-based HeteroWafer® Technology
Ultra low defect SiGe relaxed buffers
Optical Characterisation of SiGe/Si
Ultrathin SiGe Virtual substrates
SiGe on SOI for CMOS
SiGe Quantum Cascade Terahertz
Optoelectronics on Silicon
Advanced SiGe BiCMOS
SiGe vs CMOS vs GaAs for RF & wireless
Strained Si for sub 100nm CMOS
Defects, Diffusion and Dislocations in SiGe/Si
SiGe for HBT's and relaxed buffers for CMOS

Scope of the Conference

- Fundamentals of SiGe Processing; SiGe(C), SOI, CMOS, BiCMOS, OEIC.
- SiGe for MEMS RF and optical switches
- Integration issues, BiCMOS, Strained-CMOS, SOI, Carbon in SiGe, silicides and high k
- Epitaxy Fundamentals; Selectivity, surface phenomena, MBE, CVD, UHV/CVD
- Novel Device Physics; Quantum effects, HFETs
- CVD Manufacturing issues; e.g. Uniformity at 300mm, single wafer vs batch processing
- Fundamentals of Heteroepitaxial growth: strain relaxation dynamics, morphology and defects
- Silicon Germanium HBT's for bipolar and BiCMOS technology
- Strained Silicon for sub 100nm CMOS
- SiGe(C) Applications in CMOS; raised source /drains, gates
- Silicon Germanium and low T epitaxy for MEMS and SOI
- Si-based Optoelectronics and Photonics
- Self Assembly and Nanostructures, Quantum structures
- Virtual(compliant)substrates, relaxed buffers

AIXTRON